

FORM PTO-1449				Atty. Docket No. XA-9693A		Appln. No. 10/701,497	
LIST OF DOCUMENTS CITED BY APPLICANT				Applicant Yoshitaka SASAGO et al.			
				Filing Date HEREWITH 11-06-03		Group 9800	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
<i>JmJ</i>	AA	5,095,344	03/10/92	Harari (corrs. to JP 2694618)	357	23.5	
<i>JmJ</i>	AB	5,739,569	4/98	Chen	257	322	
<i>JmJ</i>	AC	5,773,863	6/98	Burr et al.	257	316	
<i>JmJ</i>	AD	6,492,690	12/02	Ueno et al.	257	316	
<i>JmJ</i>	AE	4,561,004	12/85	Kuo et al.	257	319	
<i>JmJ</i>	AF	4,745,083	5/88	Huie	257	316	
<i>JmJ</i>	AG	5,455,792	10/95	Yi	257	345	
<i>JmJ</i>	AH	5,640,032	6/97	Tomiooka	257	316	
	AI						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AJ	2694618	09/12/97	Japan			No
	AK	9 331157	12/12/97	Japan			Abstract
	AL						
	AM						
	AN						
	AO						
OTHER (including author, title, date, pertinent pages, etc.)							
	AP	"Ohyo Butsuri" (or APPLIED PHYSICS), The Japan Society of Applied Physics, Vol. 65, No. 11, November 10, 1996, pp. 1114-1124.					
	AQ	K. Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select Gate on its Source Side", IBM, 1989, pp. 603-606.					
	AR						
Examiner T. M. Thomas				Date Considered 12-01-05			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

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<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				Applicant Yoshitaka SASAGO et al.			
				Filing Date HEREWITH- 11-06-03		Group 2822	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	5,095,344	03/10/92	Harari (corrs. to JP 2694618)	357	23.5	
	AB	5,739,569	4/98	Chen	257	322	
	AC	5,773,863	6/98	Burr et al.	257	316	
	AD	6,492,690	12/02	Ueno et al.	257	316	
	AE	4,561,004	12/85	Kuo et al.	257	319	
	AF	4,745,083	5/88	Huie	257	316	
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<i>JmJ</i>	AJ	2694618	09/12/97	Japan			No
<i>JmJ</i>	AK	9-321157	12/12/97	Japan			Abstract
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	AP	"Onyo Butsuri" (or APPLIED PHYSICS), The Japan Society of Applied Physics, Vol. 65, No. 11, November 10, 1996, pp. 1114-1124.					
<i>JmJ</i>	AQ	K. Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on its Source Side", IEDM, 1989, pp. 603-606.					
	AR						
Examiner <i>J. M. Thomas</i>				Date Considered 07-07-06			
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